2983 (438/127,612,760,778).CCLS. USPAT, US-RPUB; EPC; JPO; DERWENT; IBM_TDB USPAT; US-RPUB; EPC; JPO; JPO; DERWEN	L Number	Hits	Search Text	DB	Time stamp
Section Sect			(438/127 612 760 778) CCLS.	USPAT;	
Section Sect	4	2303	(400/12/,012/100/170/.0020.	US-PGPUB;	
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250		ŀ			
18	_	050	((420)(427,642,760,778), CCLS) and (anovy adid resin)		2002/06/18 09:08
18	5	250	((438/127,612,760,776).CCLS.) and (epoxy adj+ 163m)		
18					
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1513 (625/109,523).CCLS. 1513 (625/109,394,106,395).CCLS. 1513 (625/10,93,94,106,395).CCLS. 151					2002/06/18 00:08
1513 (525/109,523).CCLS.	6	18	(((438/127,612,760,778).CCLS.) and (epoxy adj4 resin)) and		2002/00/10 03:00
7 1513 (525/109,523).CCLS. 8 896 ((525/109,523).CCLS.) and (epoxy adj4 resin) 9 11 (((525/109,523).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 10 1 1 ((525/109,523).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 10 1 1 (528/10,93,94,106,395).CCLS. 11 2 598 (((528/10,93,94,106,395).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 12 598 (((528/10,93,94,106,395).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 13 8 ((((528/10,93,94,106,395).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 14 44 ((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 15 31 ((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 16 0 (((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 16 0 (((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 17 15 31 (((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 18 19 10 (((((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 19 2002/06/18 09:26 2002/06/18 09:26 2002/06/18 09:26 2002/06/18 09:26 2002/06/18 09:26 2002/06/18 09:26 2002/06/18 09:26 2002/06/18 09:26 2002/06/18 09:26 2002/06/18 09:26 2002/06/18 09:26 2002/06/18 09:26 2002/06/18 09:26			"silicon oxide"		
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1513 (525/109,523).CCLS. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;				· ·	
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8 896 ((525/109,523).CCLS.) and (epoxy adj4 resin) 9 11 (((525/109,523).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 10 1 1 2260 (528/10,93,94,106,395).CCLS. 12 598 (((528/10,93,94,106,395).CCLS.) and (epoxy adj4 resin) 13 8 (((528/10,93,94,106,395).CCLS.) and (epoxy adj4 resin) 14 44 (523/425).CCLS.) and (epoxy adj4 resin) 15 31 (((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 16 0 ((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 16 0 ((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 17 0 ((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 18 0 ((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 18 0 ((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 19 0 ((((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 10 0 (((((((((((((((((((((((((((((((((
9 11 (((525/109,523).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; USPGPUB; EPO; JPO; DERWENT; ISM_				IBM_TDB	
9 11 (((525/109,523).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	ρ	896	((525/109 523) CCLS.) and (epoxy adi4 resin)	USPAT;	2002/06/18 09:23
9 11 (((525/109,523).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" EPO; JPO; DERWENT; IBM_TDB USPAT;	0	030	((020/100,020).0020.) and (0pon) and	US-PGPUB;	
9 11 (((525/109,523).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 2002/06/18 09:23 2002/06/18 09:23 2002/06/18 09:23 2002/06/18 09:23 2002/06/18 09:23 2002/06/18 09:23 2002/06/18 09:23 2002/06/18 09:25 2002/06/18 09:25 2002/06/18 09:25 2002/06/18 09:25 2002/06/18 09:25 2002/06/18 09:25 2002/06/18 09:25 2002/06/18 09:25 2002/06/18 09:25 2002/06/18 09:25 2002/06/18 09:25 2002/06/18 09:25 2002/06/18 09:25 2002/06/18 09:26 2002/06/18 09:2					
9 11 (((525/109,523).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 2002/06/18 09:23 USPAT: US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO;					
9 11 (((525/109,523).CCLS.) and (epoxy adj4 resin)) and "silicon oxide"					
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12 2260 (528/10,93,94,106,395).CCLS. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;				<u> </u>	2002/06/18 09:16
12 598 (((528/10,93,94,106,395).CCLS.) and (epoxy adj4 resin) 13 8 ((((528/10,93,94,106,395).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 14 44 (523/425).CCLS.) 15 31 (((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 16 0 ((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 17 0 ((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 18 0 ((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 18 0 ((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 19 0 (((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 10 0 (((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 10 0 (((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" 10 0 ((((((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide") 10 0 (((((((((((((((((((((((((((((((((10	1			
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12 598 ((528/10,93,94,106,395).CCLS.) and (epoxy adj4 resin) IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWEN			·		
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14 44 (523/425).CCLS. 15 31 ((523/425).CCLS.) and (epoxy adj4 resin) 16 0 (((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	10			US-PGPUB;	
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15 31 ((523/425).CCLS.) and (epoxy adj4 resin) 16 0 (((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	14	74	(020/720).0020.		
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16 0 (((523/425).CCLS.) and (epoxy adj4 resin)) and "silicon oxide" EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	15	31	((3231423).COLO.) and (chox) and leant)		
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DERWENT;					
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06/18/2002

FILE 'REGISTRY' ENTERED AT 08:55:12 ON 18 JUN 2002 E SILOXIRANE/CN 1 S E2 L1FILE 'HCAPLUS' ENTERED AT 08:56:15 ON 18 JUN 2002 10 S SILOXIRANE L2 1 S SILOXIRAN L30 S L1 L4FILE 'REGISTRY' ENTERED AT 09:01:29 ON 18 JUN 2002 L5 STRUCTURE UPLOADED 2 S L5 SSS SAM L6 3 S L5 SSS FULL L7FILE 'HCAPLUS' ENTERED AT 09:05:13 ON 18 JUN 2002 L83 S L7 FILE 'REGISTRY, MARPAT, MARPATPREV, CAPLUS' ENTERED AT 09:06:15 ON 18 JUN 2002 L9 2 S L7 SSS SAM FILE=REGISTRY 0 S L9 SSS SAM FILE=MARPAT FILE 'MARPAT' ENTERED AT 09:07:03 ON 18 JUN 2002 0 S L7 L11FILE 'USPATFULL, IFIPAT, IFIUDB' ENTERED AT 09:07:47 ON 18 JUN 2002 3 S L7 L120 S L12 NOT L8 L13 FILE 'BEILSTEIN' ENTERED AT 09:09:12 ON 18 JUN 2002 => S L7 0 L7 L14

- L2 ANSWER 1 OF 10 HCAPLUS COPYRIGHT 2002 ACS
- AN 2001:398133 HCAPLUS
- DN 135:227032
- TI The gas-phase reaction of silylene with acetaldehyde. Part 1. Direct rate studies, isotope effects, RRKM modeling and ab initio studies of the potential energy surface
- AU Becerra, R.; Cannady, J. P.; Walsh, R.
- CS Instituto de Quimica Fisica "Rocasolano," CSIC, Madrid, 28006, Spain
- SO Physical Chemistry Chemical Physics (2001), 3(12), 2343-2351 CODEN: PPCPFQ; ISSN: 1463-9076
- PB Royal Society of Chemistry
- DT Journal
- LA English
- Time-resolved studies of the title reaction, employing both SiH2 and SiD2, ΑB have been carried out over the pressure range 1-100 Torr (with SF6 as bath qas) at five temps. in the range 297-599 K, using laser flash photolysis to generate and monitor both silylene species. The second order rate consts. obtained were pressure dependent indicating that the reaction is a third-body assisted assocn. process. The high pressure rate consts., obtained by extrapolation, gave the following Arrhenius parameters: log(A/cm3 mol.-1 s-1) = -10.10.+-.0.06, Ea=-3.91.+-.0.47 kJ mol-1, where the uncertainties are single std. deviations. The parameters are consistent with a fast assocn. process occurring at close to the collision rate. RRKM modeling, based on a transition state appropriate to formation of a three-membered ring product, 3-methylsiloxirane, and employing a weak collisional deactivation model gives reasonable fits to the pressure dependent curves for .DELTA.H.degree./kJ mol-1 in the range -215 to -245. Ab initio calcns. at the G2 level indicate the inital formation of a silacarbonyl ylid which can then either form the siloxirane by ring closure, rearrange to form siloxyethene or give ethoxysilylene. Fuller details of the potential surface are given. The energetics are reasonably consistent with siloxirane formation representing the main pathway. The isotope effects are small and close to unity, indicating that secondary isotopic label scrambling, by the reversible ring opening of the siloxirane to ethoxysilylene is not occurring. Differences with the silirane system can be explained by the stabilization of a silylene by an alkoxy substituent.
- RE.CNT 42 THERE ARE 42 CITED REFERENCES AVAILABLE FOR THIS RECORD ALL CITATIONS AVAILABLE IN THE RE FORMAT

=> D BIB AB HITSTR 2-10

- L2 ANSWER 2 OF 10 HCAPLUS COPYRIGHT 2002 ACS
- AN 2000:612930 HCAPLUS
- DN 133:181214
- TI Pump housing coated with polymer and method therefor
- IN Choe, Sung-Soo
- PA Daewoo Electronics Co., S. Korea
- SO Repub. Korea, No pp. given
 - CODEN: KRXXFC
- DT Patent
- LA Korean
- FAN.CNT 1

	PATENT NO.	KIND DATE		APPLICATION NO.	DATE	
PΙ	KR 131532	B1	19980417	KR 1994-30018	19941116	

- The inner rough surface(2) of the hot water circulating pump housing (1) made of cast iron is defatted by washing, dried, coated primarily with tar epoxy at room temp. for 7-8 h, and coated secondarily with a siloxirane compd. to form double-layered anticorrosive polymer wherein tar epoxy layer and siloxirane compd. layer are 100 .mu.m thick and 80-120 .mu.m thick, resp.
- L2 ANSWER 3 OF 10 HCAPLUS COPYRIGHT 2002 ACS
- AN 1999:322771 HCAPLUS
- DN 131:73278
- TI Gas-Phase Reaction of Silylene with Acetone: Direct Rate Studies, RRKM Modeling, and ab Initio Studies of the Potential Energy Surface
- AU Becerra, R.; Cannady, J. P.; Walsh, R.
- CS Instituto de Quimica Fisica Rocasolano, CSIC, Madrid, 28006, Spain
- SO Journal of Physical Chemistry A (1999), 103(23), 4457-4464 CODEN: JPCAFH; ISSN: 1089-5639
- PB American Chemical Society
- DT Journal
- LA English
- Time-resolved studies of the title reaction were carried out over the ΑB pressure range 3-100 torr (with SF6 as bath gas) at 5 temps. in the range 295-602 K, using laser flash photolysis to generate and monitor silylene, SiH2. The 2nd-order rate consts. obtained were pressure-dependent, indicating that the reaction is a 3rd-body-assisted assocn. process. high-pressure rate consts., obtained by extrapolation, gave the following Arrhenius parameters: log(A/cm3 mol.-1 s-1) = -10.17 .+-. 0.04 and Ea = -4.54 .+-. 0.32 kJ mol-1, where the uncertainties are single std. deviations. The parameters are consistent with a fast assocn. process therhead occurring at close to the collision rate. RRKM modeling, based on a transition state appropriate to formation of a 3-membered ring product, 3,3-dimethylsiloxirane, and employing a weak collisional deactivation model, gives reasonable fits to the pressure-dependent curves for .DELTA.H.degree./kJ mol-1 in the range -205 to -225. Ab initio calcns. at the G2 level indicate the initial formation of a silacarbonyl ylide, which can then either form the **siloxirane** by ring closure or rearrange to form 2-siloxypropene. Fuller details of the potential surface are The energetics are consistent with siloxirane formation representing the main pathway.
- RE.CNT 49 THERE ARE 49 CITED REFERENCES AVAILABLE FOR THIS RECORD ALL CITATIONS AVAILABLE IN THE RE FORMAT
- L2 ANSWER 4 OF 10 HCAPLUS COPYRIGHT 2002 ACS
- AN 1998:777071 HCAPLUS
- DN 130:84306
- TI Interpretation of temporary impedance increases of steel/polymer coating systems in electrolytes
- AU Klenowicz, Zbigniew; Miszczyk, Andrzej; Darowicki, Kazimierz
- CS Politech. Gdanska, Gdansk, 80-952, Pol.
- Prace Naukowe Instytutu Technologii Nieorganicznej i Nawozow Mineralnych Politechniki Wrocławskiej (1998), 46, 143-148
 CODEN: PNPWAP; ISSN: 0084-2893
- PB Oficyna Wydawnicza Politechniki Wroclawskiej
- DT Journal
- LA Polish
- AB Examples of temporary impedance heightening of coating systems having 60-1800 gm in thickness during exposure to 3% NaCl, 36% HCl and 40% NaOH at room temp. and to 70% H2SO4 at 353K are presented. Three types of coatings were tested, namely vinyl, epoxy and siloxirane. The possible reasons of such spontaneous impedance increases were analyzed.

Possibilities of coating tightness improvements due to polymn., swelling, filling of pores with hydrogen evolved or self healing with corrosion products were taken into account. Filling the pores with rust formed as a result of corrosion reaction performed at the pore bottoms is with the highest probability the reason of spontaneous impedance growth during exposure.

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ANSWER 5 OF 10 HCAPLUS COPYRIGHT 2002 ACS
L2
    1998:387441 HCAPLUS
ΑN
DN
    129:69204
    New generation of polymer lining systems for cargo tanks
ΤI
    Keehan, D. J.
ΑU
     Advanced Polymer Sciences Inc., Avon, OH, USA
CS
    British Corrosion Journal (1997) 32(3), 174-178
SO
    CODEN: BCRJA3; ISSN: 0007-0599
    Institute of Materials
PB
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DT Journal

LA English

Advanced Polymer Sciences (APS) originally developed Siloxirane, a patented multifunctional polymer with a high d. crosslinked structure, to meet the extremely demanding anticorrosion and surface protection requirements of the military and aerospace industries. The superior performance of the material has also made it attractive as a coating in a wide range of marine and industrial applications. Not the least of these is its use as the lining material for the cargo tanks of seagoing chem. tankers, an area in which there were no real technol. advances for .gtoreq.20 yr. Researchers at APS have conducted .gtoreq.5000 tests on Siloxirane - as well as conventional coating systems such as epoxies, Zinc silicates, vinyl esters, rubbers, and phenolics - to test phys. properties and chem. resistance for an extensive range of products, including those commonly carried by sea.

- L2 ANSWER 6 OF 10 HCAPLUS COPYRIGHT 2002 ACS
- AN 1997:145190 HCAPLUS
- DN 126:157542
- TI Experimental and Theoretical Characterization of FSi(OCH3)2(OCH2)-: A Gas Phase Fluoride-Siloxirane Adduct
- AU Morgon, Nelson H.; Argenton, Andre B.; da Silva, Maria L. P.; Riveros, Jose M.
- CS Institute of Chemistry, University of Sao Paulo, Sao Paulo, 05599-970,
 Brazil
- SO J. Am. Chem. Soc. (1997), 119(7), 1708-1716 CODEN: JACSAT; ISSN: 0002-7863
- PB American Chemical Society
- DT Journal
- LA English
- The structural characteristics and reactivity of the gas-phase FSi(OCH3)2(OCH2) ion were studied by a combination of ab initio calcns. and FT-ICR techniques. The theor. calcns. for different possible structures reveal that carbanion and alkoxide ion type structures lead to ring closure upon geometry optimization to yield two different cyclic fluoride-siloxirane structures. The FSi(OCH3)2(cyc-OCH2) ions contg. the elusive siloxirane ring are extremely stable with respect to F- (69 kcal mol-1) dissocn. in agreement with earlier calcns. on simpler systems. Exptl., this ion is formed as a minor product (7%) in the gas-phase ion/mol. reaction of F- with Si(OMe)4 and undergoes readily fluoride transfer to the parent neutral. This strongly suggests an ion with a structure corresponding to a fluoride adduct of a siloxirane species. Reaction of FSi(OCH3)2(OCH2) with BF3,

hexafluorobenzene, and gas-phase acids more acidic than EtOH further suggests that this ion is capable of reacting as an alkoxide type nucleophile or base. This latter behavior was assocd. with the possibility of ring opening of the **siloxirane** in the collision complex that mediates this ion/mol. reaction.

- L2 ANSWER 7 OF 10 HCAPLUS COPYRIGHT 2002 ACS
- AN 1996:716883 HCAPLUS
- TI Siloxirane based polymer coating for slop tanks
- AU Anon.
- SO Br. Corros. J. (1996), 31(3), 168 CODEN: BCRJA3; ISSN: 0007-0599
- DT Journal; Miscellaneous
- LA English
- AB Unavailable
- L2 ANSWER 8 OF 10 HCAPLUS COPYRIGHT 2002 ACS
- AN 1996:259696 HCAPLUS
- DN 125:10921
- TI Reactions of a Silanediyl with Carbon-Oxygen and Carbon-Nitrogen Double Bonds
- AU Belzner, Johannes; Ihmels, Heiko; Pauletto, Lara; Noltemeyer, Matthias
- CS Institut fuer Organische Chemie, Georg-August-Universitaet, Goettingen, D-37077, Germany
- SO J. Org. Chem. (1996), 61(10), 3315-19 CODEN: JOCEAH; ISSN: 0022-3263
- DT Journal
- LA English
- OS CASREACT 125:10921
- Silanediyl ((2-(Me2NCH2)C6H4)2Si: or Ar2Si:, 2) (generated by thermolysis of the corresponding cyclotrisilane) reacts with benzophenone, tetracyclone, and fluorenone to yield products I (X = 0), II and III, resp., which may originate from highly reactive siloxiranes as intermediates. However, using adamantanone as ketone, stable siloxirane IV was obtained. The interaction of 2 with benzophenone anil or fluorenone 2,6-dimethylanil gives heterocyclic compds. I (X = NH) and V, resp. The involvement of silaziridines in these reactions, as well as in the reactions of 1 with 1,4-diaza-1,3-butadienes, which yield the expected formal [4 + 1] cycloaddn. products VI (R = tBu, cyclohexyl), remains questionable. Results of x-ray crystallog. structure detns. of II and VI (R = tBu) are available form the Cambridge Crystallog. Data Center.
- L2 ANSWER 9 OF 10 HCAPLUS COPYRIGHT 2002 ACS
- AN 1994:220444 HCAPLUS
- DN 120:220444
- TI New generation polymers to replace epoxies, vinyl esters, and phenolics
- AU Keehan, Donald J.
- CS Adv. Polym. Sci., Inc., Australia
- SO Conf. Australas. Corros. Assoc. (1991), 31st(Corrosion 91), Paper C5, 14 pp.
 - CODEN: CEANDQ; ISSN: 0729-2341
- DT Journal
- LA English
- AB The advantages of chem. resistant polymers based on pentafunctional (arom. oxirane) end-capped cyclic Si oxide (Siloxirane), as coatings, over epoxy, epoxy acrylate, and bismaleimide resins were discussed.
- L2 ANSWER 10 OF 10 HCAPLUS COPYRIGHT 2002 ACS

Serial No.:09/844,855

06/18/2002

- AN 1993:451370 HCAPLUS
- DN 119:51370
- TI AC-impedance measurements on coatings for desulfurization plants
- AU Oestergaard, M. J. L.; Visgaard, A.; Maahn, E.
- CS Mater. Dep., Risoe Natl. Lab., Roskilde, 4000, Den.
- SO Surf. Coat. Int. (1993), 76(1), 29-30, 32-4, 36-9 CODEN: SCOIE6
- DT Journal
- LA English
- Degrdn. of coatings (glass flake-filled vinyl ester resins, chlorinated AB butyl rubber, epoxy, siloxane, fluoropolymer, fluoro-contg. rubber) for FGD plants was investigated by impedance measurements. The resistance of coatings is high and the capacitance low as long as the coating does not show any degrdn. When degrdn. begins, impedance measurements quickly indicate changes in resistance and capacitance even if the damage zones are small. The impedance measurements indicate also degrdn. trends in coatings; in some cases, degrdn. starts with formation of pores with further diffusion-controlled electrochem. processes. These processes manifest as a drastic decrease in the resistance and increase in total impedance and phase angle at low frequencies when the process is controlled by diffusion. In other cases, the impedance decreased at low frequencies, which was attributed to formation of active sites in the form of blisters or cracks. Control of use of rubber coatings in 3% Cl solns. is recommended since degrdn. can begin after short exposure time (about 80 days). Glass filled-vinyl esters withstand this media in the studied temp. range. Degrdn. of coatings in 70% H2SO4 at 100.degree. starts immediately and ends by complete disappearance of coatings in 4-7 days. Glass-filled vinyl ester coatings withstand H2SO4 media during 50 days. It was impossible to perform electrochem. measurements of siloxirane coating due to the absence of the electrolytic contact through the coating under the studied conditions.

L3 ANSWER 1 OF 1 HCAPLUS COPYRIGHT 2002 ACS

AN 1996:73220 HCAPLUS

DN 124:120289

TI Hybrid prepolymer-based coatings and their manufacture

IN Sakurai, Kazuhisa; Oana, Tomoharu; Aihara, Tetsuo

PA Abc Trading Co, Japan

SO Jpn. Kokai Tokkyo Koho, 7 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

PATENT NO. KIND DATE APPLICATION NO. DATE

PI JP 07292315 A2 19951107 JP 1994-83425 19940421

AB In order to adjust the viscosity without impairing the prepolymer properties, title coatings contain polyepoxy diluents and amine hardeners. A mixt. of Siloxiran (cyclic silicone/epoxy resin hybrid prepolymer) 100, neopentyl glycol diglycidyl ether 20, and a modified aliph. polyamine 25 showed 20.degree. viscosity 2500 cP, pencil hardness 4, and good chem. (concd. H2SO4, Me2CO, and MEK) resistance.

=> D L5

L5 HAS NO ANSWERS

 L_5

STR



G1 Ak,H

G2 Cy,Ak

ANSWER 1 OF 3 HCAPLUS COPYRIGHT 2002 ACS L8 1996:106720 HCAPLUS AN DN 124:261966 Selective monoaddition to siloxanes and poly(dihydrosiloxanes) as TIintermediates or coating precursors Crivello, James V. IN PΑ Polyset Company, Inc., USA U.S., 9 pp. SO CODEN: USXXAM DT Patent English LA FAN.CNT 1 KIND DATE APPLICATION NO. DATE PATENT NO. ----US 5484950 Α 19960116 US 1992-993689 19921221 PΙ OS MARPAT 124:261966 An olefin, e.g. 3-vinyl-7-oxabicyclo[4.1.0] heptane (I) or acetylene is AΒ added to a siloxane which contains 2 reactive Si-H bonds to produce unsym. siloxanes (monoaddn. product) from sym. dihydrosiloxanes. A second olefin or acetylene may be added to the remaining H terminal group to produce a product with two functional groups, e.g. diepoxide compd. Thus, 1,1,3,3-tetramethyldisiloxane (0.1 mol) and I (0.05 mol) were heated at 50-55.degree. for 3 h in the presence of Pt hydrosilation catalyst to give a product b. 65.degree. (0.03 mm Hg). ΙT 175647-04-8P RL: IMF (Industrial manufacture); PREP (Preparation) (selective monoaddn. to siloxanes for functional intermediates or coating precursors)

Disiloxane, 1,1,3,3-tetramethyl-1-[2-(1-methyl-7-oxabicyclo[4.1.0]hept-3-

175647-04-8 HCAPLUS

yl)propoxy] - (9CI) (CA INDEX NAME)

ANSWER 2 OF 3 HCAPLUS COPYRIGHT 2002 ACS 1.8 1987:18807 HCAPLUS ΑN DN 106:18807 ΤI Aminosilane coupling agents Inokuchi, Hiroichi; Watanabe, Akihiko; Yoshida, Shinjiro; Yoshii, Tadashi; IN

Yonaiyama, Hiroshi Nitto Boseki Co., Ltd., Japan; Nippon Unicar Co., Ltd. PA

Jpn. Kokai Tokkyo Koho, 7 pp.

SO

CODEN: JKXXAF

=> D BIB AB HITSTR 2-3

DT Patent

LA Japanese

FAN.CNT 1

RN

CN

PATENT NO. KIND DATE APPLICATION NO. DATE

PI JP 61112086 A2 19860530 JP 1984-233677 19841106 JP 01013714 B4 19890307

OS CASREACT 106:18807

The title coupling agents comprise aminosilanes (RNHZNR1Z1Z2)mSi(OR2)4-m AΒ (I; Z = arom. hydrocarbon group; Z1 = hydrocarbon group; Z2 = C1-6 aliph. hydrocarbon group; R = H, C1-4 hydrocarbon group; R1 = H, C1-4 hydrocarbon group, arom. hydrocarbon group; R2 = H, C1-4 hydrocarbon group; m = 1-3) and/or I hydrohalides. I are heat-resistant and are suitable for treating glass fibers in the manuf. of laminates for electronic parts. Thus, 297.5 parts 4,4'-diaminodiphenylmethane and 832.9 parts Me2SO were heated to 130.degree. under N, 369.6 g .beta.-(3,4-epoxycyclohexyl)ethyltrimethoxysi lane was added dropwise over 1 h, and the mixt. was refluxed at 130.degree. for .gtoreq.10 h to give I (R, R1 = H, R2 = Me, Z = 4/4'-C6H4CH2C6H4, Z1 = 6-hydroxy-1,3-cyclohexylidene, Z2 = CH2CH2, m = 1). Laminate prepd. from Epikote 1045-A-70 and glass cloth impregnated with I showed no change in a pressure cooker test at 133.degree. after 180 min, and water absorption of 0.81% after 24-h immersion in H2O following the test.

IT 105822-30-8

RL: RCT (Reactant)

(reaction of, with diamines)

RN 105822-30-8 HCAPLUS

CN Silicic acid (H4SiO4), trimethyl 2-(7-oxabicyclo[4.1.0]hept-3-yl)ethyl ester (9CI) (CA INDEX NAME)

$$\begin{array}{c} \text{OMe} \\ | \\ \text{CH}_2 - \text{CH}_2 - \text{O} - \text{Si} - \text{OMe} \\ | \\ \text{OMe} \end{array}$$

L8 ANSWER 3 OF 3 HCAPLUS COPYRIGHT 2002 ACS

AN 1975:124742 HCAPLUS

DN 82:124742

TI Organosilicon compounds

IN Foley, Kevin M.; Vigo, Francesco M.

PA Owens-Corning Fiberglas Corp.

SO Ger. Offen., 69 pp.

CODEN: GWXXBX

DT Patent

LA German

FAN.CNT 4

T. WITA * A	CNII					
	PATENT NO.	KIND DATE		APPLICATION NO.	DATE	
ΡI	DE 2415395	A1	19741017	DE 1974-2415395	19740329	
	US 3931266	Α	19760106	US 1973-347241	19730402	
	BE 813082	A1	19740715	BE 1974-142669	19740329	
	FR 2223376	A1	19741025	FR 1974-11025	19740329	
	JP 49127928	A2	19741207	JP 1974-37313	19740402	
	GB 1419912	A	19751231	GB 1974-14594	19740402	
PRAI	US 1973-347241		19730402			

AB Complex siloxanes (26) were prepd. by treating a Si halide with a monoepoxide and a polyepoxide. Thus, SiCl4 was treated with 3 epoxide equivs. PhOZ (Z = glycidyl), then with 2 epoxide equivs. ZO(CH2)4OZ, and

the whole kept 1 hr to give a mixt. from which (PhOCH2CHClCH2O)3SiOCH2CHClCH2O(CH2)4OZ could be isolated.

IT 54898-93-0P

RN 54898-93-0 HCAPLUS

CN Silicic acid (H4SiO4), 2-chloro-2-(7-oxabicyclo[4.1.0]hept-3-yl)ethyl tris[2-chloro-3-(2-propenyloxy)propyl] ester (9CI) (CA INDEX NAME)